

SLPS209A - AUGUST 2009-REVISED MAY 2010

# P-Channel NexFET™ Power MOSFET

Check for Samples: CSD23201W10

#### **FEATURES**

- Ultra Low Qg and Qgd
- Small Footprint 1mm × 1mm
- Low Profile 0.62mm Height
- Pb Free
- Gate ESD Protection 3kV
- RoHS Compliant
- Halogen Free

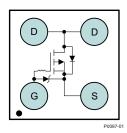
### **APPLICATIONS**

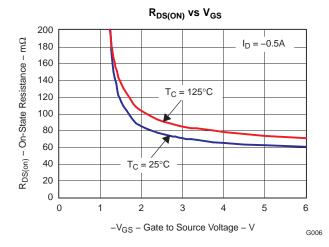
- Battery Management
- Load Switch
- Battery Protection

### **DESCRIPTION**

The device has been designed to deliver the lowest on resistance and gate charge in the smallest outline possible with excellent thermal characteristics in an ultra low profile.

### **Top View**





#### PRODUCT SUMMARY

$V_{DS}$	Drain to Source Voltage	-12		٧
$Q_g$	Gate Charge Total (4.5V)	1.8		nC
$Q_{gd}$	Gate Charge Gate to Drain	0.26		nC
		$V_{GS} = -1.5V$	110	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V$	77	mΩ
		$V_{GS} = -4.5V$	66	mΩ
V <sub>GS(th)</sub>	Threshold Voltage	-0.6		V

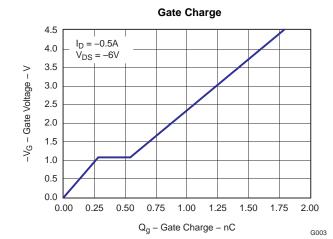
#### ORDERING INFORMATION

Device	Package	Media	Qty	Ship
CSD23201W10	1 x 1 Wafer Level Package	7-inch reel	3000	Tape and Reel

#### **ABSOLUTE MAXIMUM RATINGS**

1.202212					
T <sub>A</sub> = 2	5°C unless otherwise stated	VALUE	UNIT		
$V_{DS}$	Drain to Source Voltage	-12	V		
$V_{GS}$	Gate to Source Voltage	-6	V		
I <sub>D</sub>	Continuous Drain Current, T <sub>C</sub> = 25°C <sup>(1)</sup>	-2.2	Α		
$I_{DM}$	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	-8.8	Α		
	Continuous Gate Clamp Current	-0.5	Α		
I <sub>G</sub>	Pulsed Gate Clamp Current	<b>-</b> 7	Α		
P <sub>D</sub>	Power Dissipation <sup>(1)</sup>	1	W		
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C		

- (1)  $R_{\theta JA} = 100$  °C/W on  $1 \text{in}^2$  Cu (2 oz.) on 0.060" thick FR4 PCB.
- (2) Pulse width  $\leq 300 \mu s$ , duty cycle  $\leq 2\%$





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These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

### **ELECTRICAL CHARACTERISTICS**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Static Cl	naracteristics				,	
BV <sub>DSS</sub>	Drain to Source Voltage	$V_{GS} = 0V, I_D = -250\mu A$	-12			V
BV <sub>GSS</sub>	Gate to Source Voltage;	$V_{DS} = 0V, I_{G} = -250\mu A$	-6.1		-7.2	V
I <sub>DSS</sub>	Drain to Source Leakage Current	$V_{GS} = 0V, V_{DS} = -9.6V$			-1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{DS} = 0V, V_{GS} = -6V$			-100	nA
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	-0.4	-0.6	-1.0	V
		$V_{GS} = -1.5V, I_D = -0.5A$		110	138	mΩ
R <sub>DS(on)</sub>	Drain to Source On Resistance	$V_{GS} = -2.5V$ , $I_D = -0.5A$		77	96	mΩ
		$V_{GS} = -4.5V$ , $I_D = -0.5A$		66	82	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = -6.0V, I_{D} = -0.5A$		9		S
Dynamic	: Characteristics				,	
C <sub>ISS</sub>	Input Capacitance			250	325	pF
Coss	Output Capacitance	$V_{GS} = 0V, V_{DS} = -6.0V, f = 1MHz$		125	155	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			32	42	pF
Qg	Gate Charge Total (-4.5V)			1.8	2.4	nC
$Q_{gd}$	Gate Charge Gate to Drain	V 00V I 05A		0.26		nC
Q <sub>gs</sub>	Gate Charge Gate to Source	$V_{DS} = -6.0V, I_{D} = -0.5A$		0.28		nC
Q <sub>g(th)</sub>	Gate Charge at Vth			0.11		nC
Q <sub>OSS</sub>	Output Charge	$V_{DS} = -6.0V, V_{GS} = 0V$		1.7		nC
t <sub>d(on)</sub>	Turn On Delay Time			24		ns
t <sub>r</sub>	Rise Time	$V_{DS} = -6.0V$ , $V_{GS} = -2.5V$ , $I_{D} = -0.5A$		19		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$R_G = 20\Omega$		68		ns
t <sub>f</sub>	Fall Time			29		ns
Diode Cl	haracteristics				•	
V <sub>SD</sub>	Diode Forward Voltage	$I_S = -0.5A$ , $V_{GS} = 0V$		-0.77	-1.0	V
Q <sub>rr</sub>	Reverse Recovery Charge	$V_{dd}$ = -4.0V, $I_F$ = -0.5A, $di/dt$ = 100A/ $\mu$ s		2		nC
t <sub>rr</sub>	Reverse Recovery Time	$V_{dd} = -4.0V$ , $I_F = -0.5A$ , $di/dt = 100A/\mu s$		9.5		ns

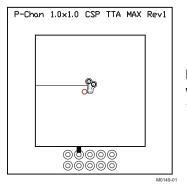
## THERMAL CHARACTERISTICS

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

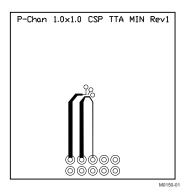
	PARAMETER	MIN	TYP	MAX	UNIT
R $_{\theta JC}$	Thermal Resistance Junction to Ambient (Minimum Cu area)			245	°C/W
R <sub>θJA</sub>	Thermal Resistance Junction to Ambient (1 in <sup>2</sup> Cu area)			125	°C/W

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Max  $R_{\theta JA} = 125^{\circ}C/W$  when mounted on 1inch<sup>2</sup> of 2 oz. Cu.



Max  $R_{\theta JA} = 245^{\circ}\text{C/W}$  when mounted on minimum pad area of 2 oz. Cu.

## TYPICAL MOSFET CHARACTERISTICS

(T<sub>A</sub> = 25°C unless otherwise stated)

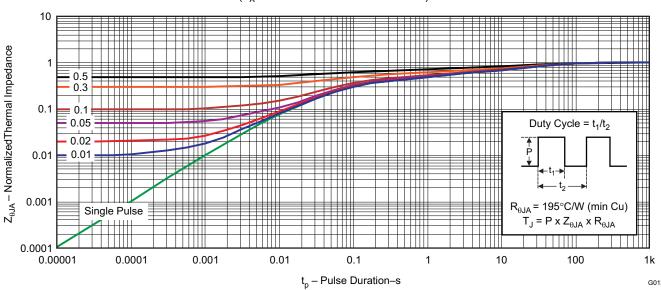


Figure 1. Transient Thermal Impedance



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

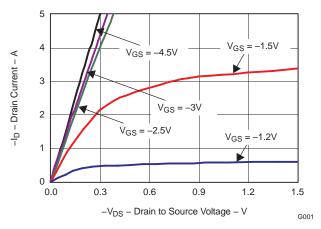


Figure 2. Saturation Characteristics

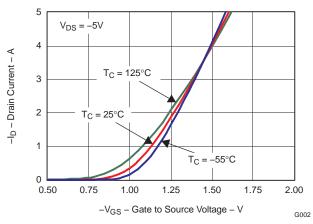


Figure 3. Transfer Characteristics

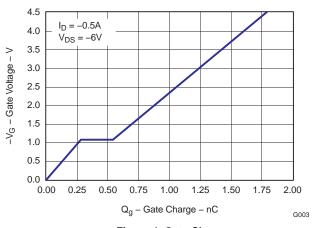


Figure 4. Gate Charge

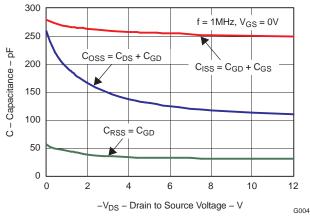


Figure 5. Capacitance

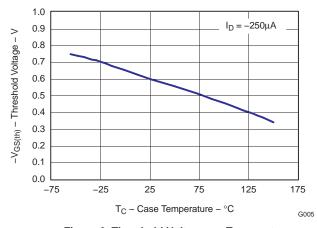


Figure 6. Threshold Voltage vs. Temperature

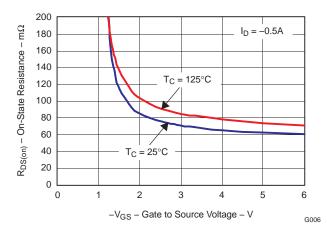


Figure 7. On Resistance vs. Gate Voltage



## **TYPICAL MOSFET CHARACTERISTICS (continued)**

## $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

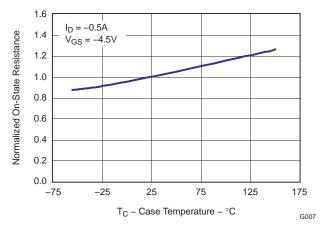


Figure 8. On Resistance vs. Temperature

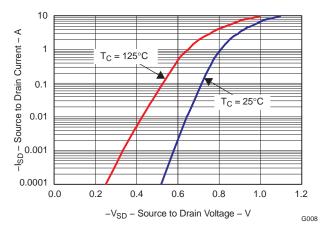


Figure 9. Typical Diode Forward Voltage

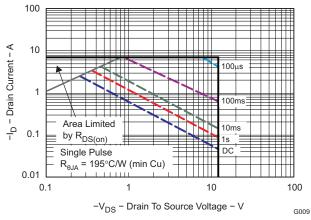


Figure 10. Maximum Safe Operating Area

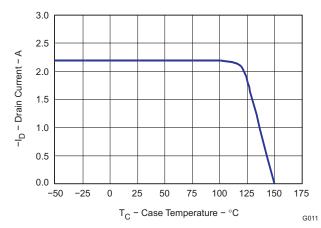
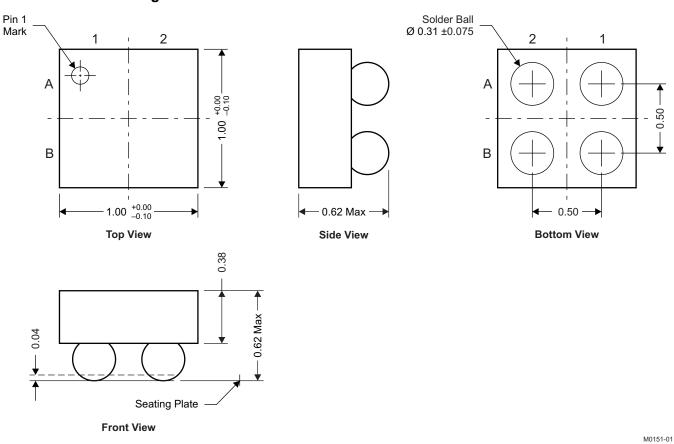


Figure 11. Maximum Drain Current vs. Temperature



## **MECHANICAL DATA**

# CSD23201W10 Package Dimensions



NOTE: All dimensions are in mm (unless otherwise specified)

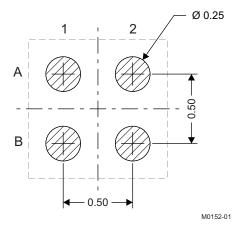
## **Pin Configuration Table**

POSITION	DESIGNATION	
B1	Source	
A1	Gate	
A2, B2	Drain	

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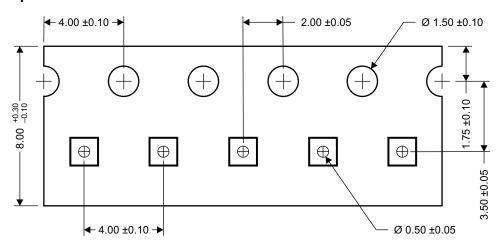


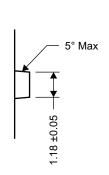
### **Land Pattern Recommendation**

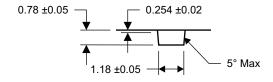


NOTE: All dimensions are in mm (unless otherwise specified)

## **Tape and Reel Information**







M0153-01

NOTE: All dimensions are in mm (unless otherwise specified)

## **REVISION HISTORY**

## Changes from Original (August 2009) to Revision A

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